

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (L²-π-MOSV)

2SK2400

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

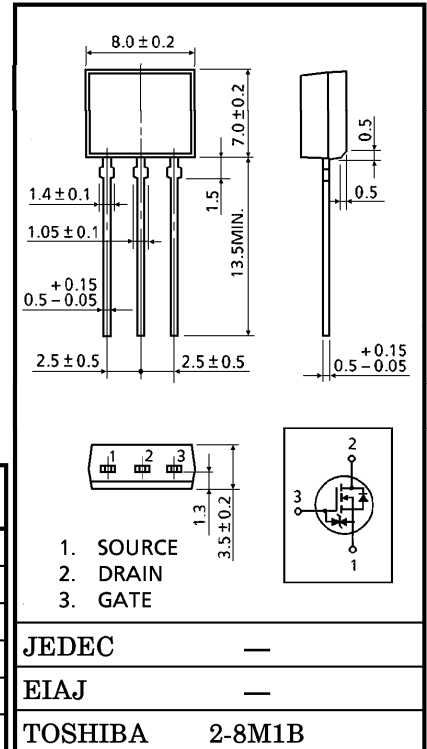
INDUSTRIAL APPLICATIONS

Unit in mm

- 4 V Gate Drive
- Low Drain-Source ON Resistance : $R_{DS(ON)} = 0.17 \Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 4.5 S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100 \mu A$ (Max.) ($V_{DS} = 100 V$)
- Enhancement-Mode : $V_{th} = 0.8 \sim 2.0 V$
($V_{DS} = 10 V, I_D = 1 mA$)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	100	V
Drain-Gate Voltage ($R_{GS} = 20 k\Omega$)		V_{DGR}	100	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	5	A
	Pulse	I_{DP}	20	A
Drain Power Dissipation ($T_c = 25^\circ C$)		P_D	1.3	W
Single Pulse Avalanche Energy**		E_{AS}	180	mJ
Avalanche Current		I_{AR}	5	A
Repetitive Avalanche Energy*		E_{AR}	0.13	mJ
Channel Temperature		T_{ch}	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C



Weight : 0.55 g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	96.1	°C/W

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 25 V, T_{ch} = 25^\circ C$ (initial), $L = 11.6 mH, R_G = 25 \Omega, I_{AR} = 5 A$

This transistor is an electrostatic sensitive device.

Please handle with caution.

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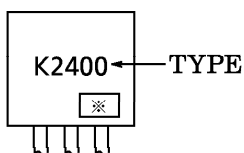
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	—	—	±10	μA
Drain Cut-off Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V	—	—	100	μA
Drain-Source Breakdown Voltage	V _{(BR) DSS}	I _D = 10 mA, V _{GS} = 0 V	100	—	—	V
Gate Threshold Voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	0.8	—	2.0	V
Drain-Source ON Resistance	R _{DS (ON)}	V _{GS} = 4 V, I _D = 2.5 A	—	0.22	0.30	Ω
		V _{GS} = 10 V, I _D = 2.5 A	—	0.17	0.23	
Forward Transfer Admittance	Y _{fs}	V _{DS} = 10 V, I _D = 2.5 A	2.0	4.5	—	S
Input Capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	—	500	—	pF
Reverse Transfer Capacitance	C _{rss}		—	80	—	
Output Capacitance	C _{oss}		—	190	—	
Switching Time	Rise Time	t _r		—	17	ns
	Turn-on Time	t _{on}		—	25	
	Fall Time	t _f		—	50	
	Turn-off Time	t _{off}		—	195	
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q _g	V _{DD} ≅ 80 V, V _{GS} = 10 V, I _D = 5 A	—	22	—	nC
Gate-Source Charge	Q _{gs}	—	—	15	—	
Gate-Drain (“Miller”) Charge	Q _{gd}	—	—	7	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I _{DR}	—	—	—	5	A
Pulse Drain Reverse Current	I _{DRP}	—	—	—	20	A
Diode Forward Voltage	V _{DSSF}	I _{DR} = 5 A, V _{GS} = 0 V	—	—	-1.7	V
Reverse Recovery Time	t _{rr}	I _{DR} = 5 A, V _{GS} = 0 V	—	160	—	ns
Reverse Recovery Charge	Q _{rr}	dI _{DR} / dt = 50 A / μs	—	0.28	—	μC

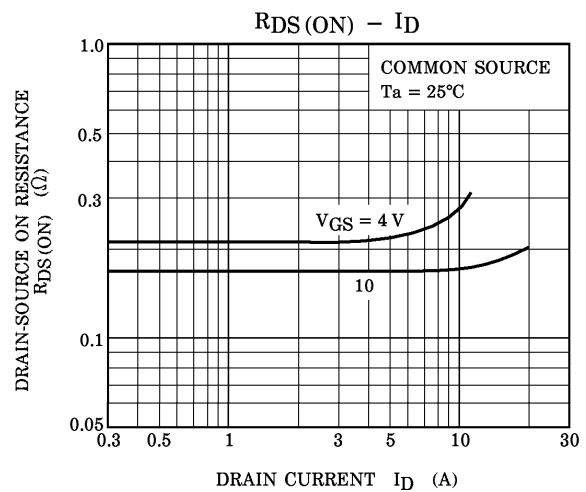
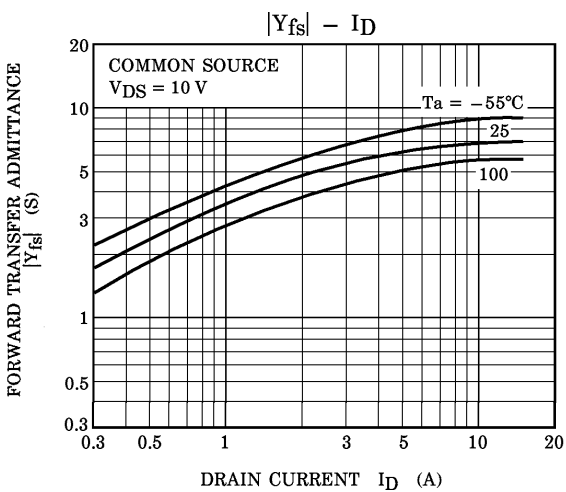
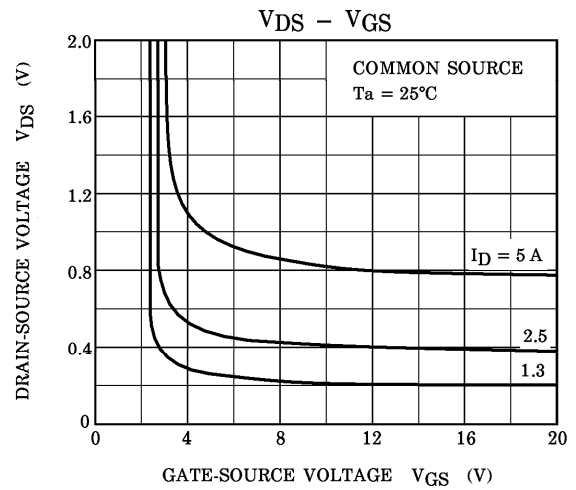
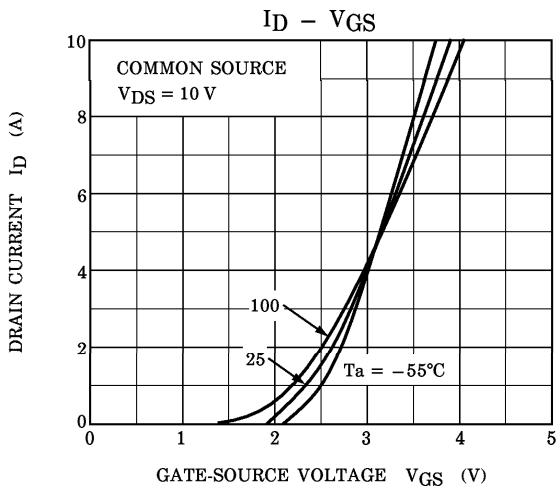
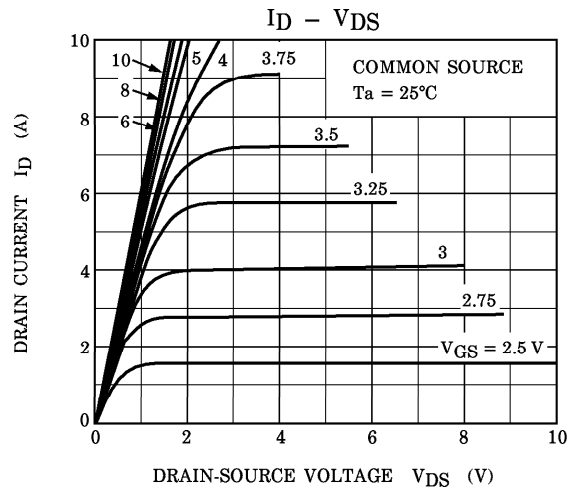
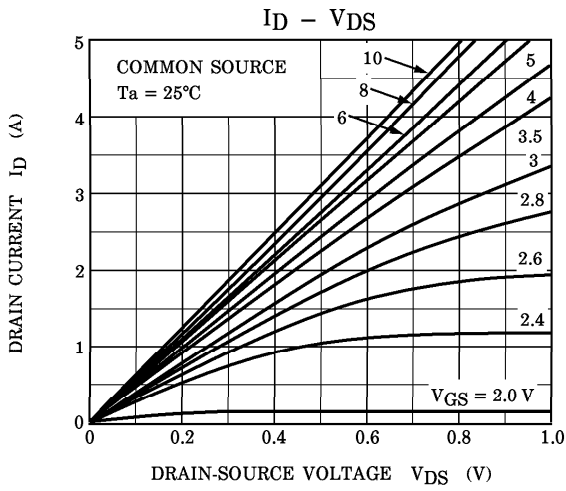
MARKING

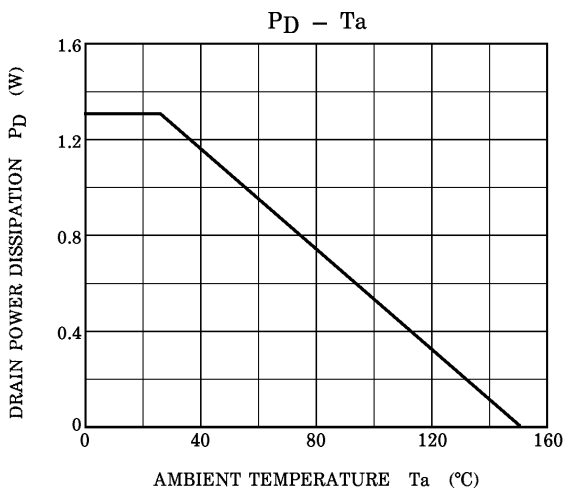
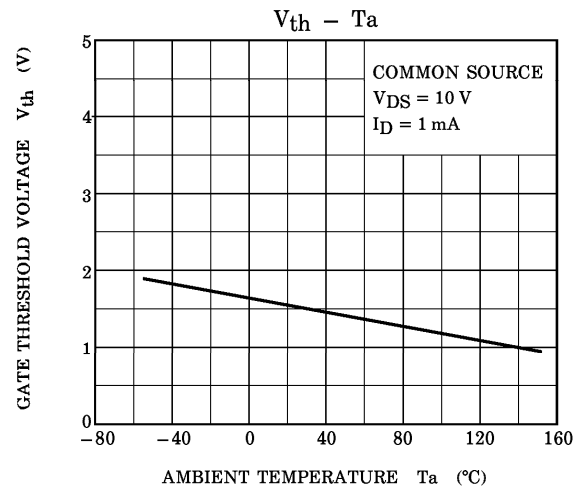
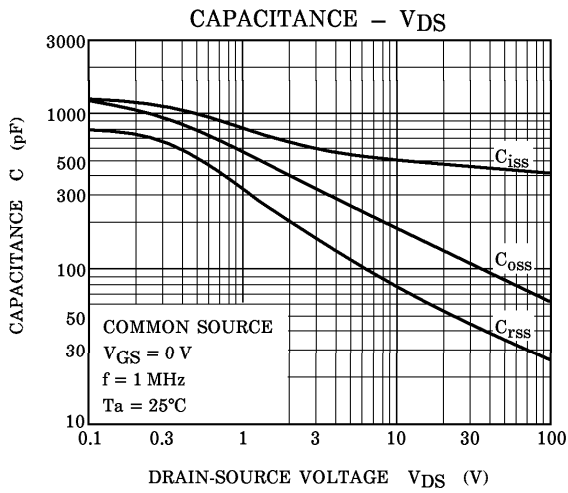
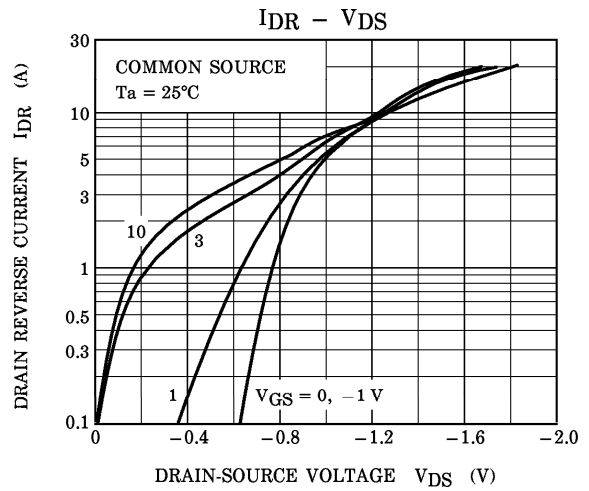
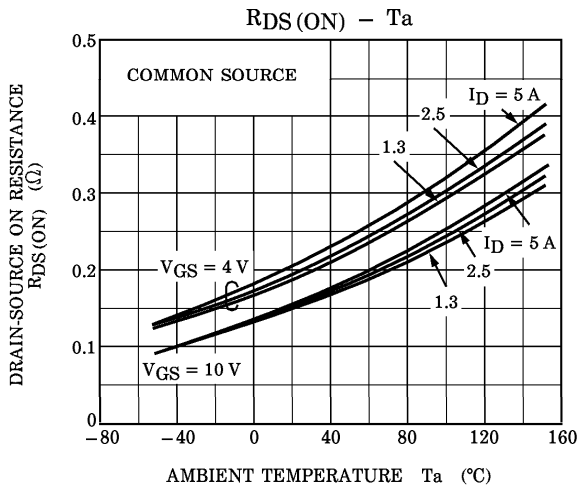


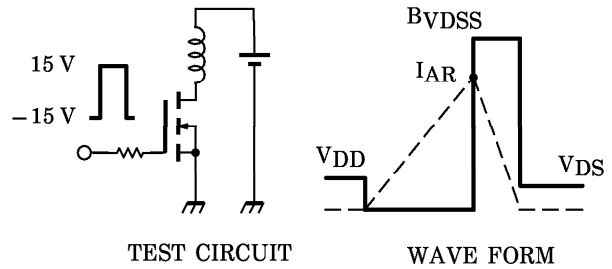
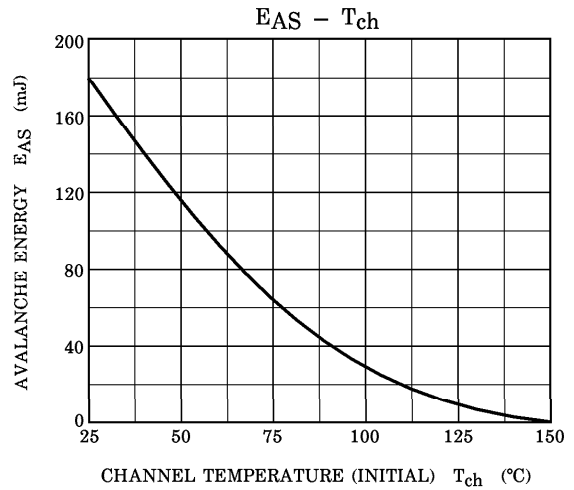
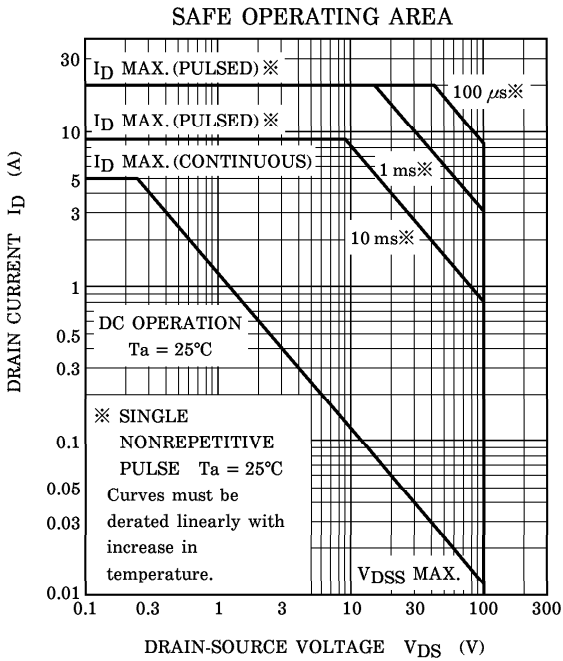
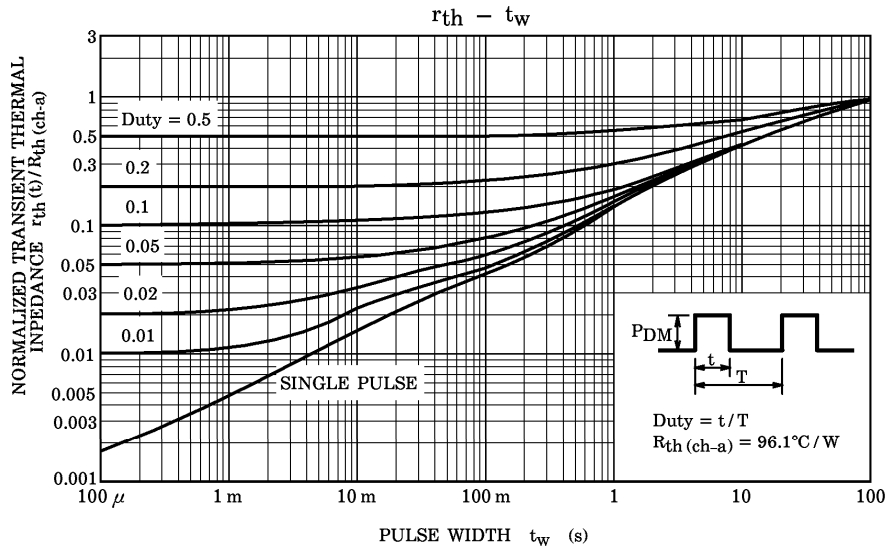
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







Peak $I_{AR} = 5 A$, $R_G = 25 \Omega$
 $V_{DD} = 25 V$, $L = 11.6 mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$